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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
AA	S.S.K. Iyer et al., "Separation by Plasma Implantation of Oxygen (SPIMOX) operational phase space," IEEE trans. On Plasma Science, Vol. 25, No.5, pp. 1128-135, 1997				
AB	G.A. Garcia et al, High Quality in Thin (100nm) Silicon on Sapphire," IEEE Trans Electron Devices vol. no. 9, no. 1, pp. 32-34, Jan. (1988)				
AC	E. Cartagena, G. Garcia, G. Imthurn, G. Kelley, H. Walker and L. Forbes, "Bonded Etchback Silicon on Sapphire Bipolar Junction Transistors," Abstracts of ECS meeting, May 1993, Honolulu, Hawaii, P. 1199.				
AD	G.P. Imthurn, G.A. Garcia, H.W. Walker, and L. Forbes, "Bonded Silicon-On-Sapphire Wafers and Devices", J. Appl. Phys., 72(6), 15 September 1992, pp. 2526-2527				
AE	P. Ball, "A Small Mountain of Materials Goes into Every Microchip," Nature Science Update, 19 Nov. 2002, http://www.nature.com/nsu/-21028/021028-12.html				
AF	"Materials Selector", Reinhold Publishing Co., Penton/IPC. http://www.handyharmancanada.com/TheBrazingBook/comparis.htm 12/02				
AG	Company page http://www.hithermaln.com/datasheets/index.cfm?page=values 12/02				
AH	R. People et al, "Calculation of Critical Layer Thickness Versus Lattice Mismatch for Ge ₂ Si _{1-x} /Si Strained Layer Heterostructures," Appl. Phys. Letters, Vol. 47, P. 322-324, August 1985.				
AI	R. People et al, "Erratum: Calculation of Critical Layer Thickness Versus Lattice Mismatch for Ge ₂ Si _{1-x} /Si Strained Layer Heterostructures," Appl. Phys. Letters, Vol. 49, P. 229, July 1986.				
AJ	G. Grenet et al., "Testing the Feasibility of Strain Relaxed Compliant Substrates," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, P.8.				
AK	K.D. Hobart et al, "High Ge-Content Relaxed Si _{1-x} Ge _x Layers by Relaxation on Compliant Substrate with Controlled Oxidation," Abstract of Electronic Materials Conferences, Santa Barbara, June 2002, pp. 8.				
AL	P. Moran et al., "Strain Relaxation in Wafer-bonded SiGe/Si Heterostructures Due to the Viscous Flow of an Underlying Borosilicate Glass," Abstract of Electronic Materials Conference, Santa Barbara, June 2002, pp. 8-9				
AM	A.J. Auberton-Herve, "SOI: Materials to Systems," Digest of the International Electron Device Meeting, San Francisco, December 1996, pp. 5-10				
AN	T. Tsuchida et al., "Self-combustion Reaction Induced by Mechanical Activation of Al-si-c Powder Mixtures," European Journal of Solid State and Inorganic Chemistry (France), Vol. 32, No. 7-8, pp. 629-38, 1995.				
AO	H.C. Yi, et al, "Combustion Synthesis of Aluminoborate Glass Matrices," J. Mater. Synth. Process. (USA), Vol. 8, No. 1, pp. 15-20, Jan. 2000.				
AP	Dip. -Ing. M. Wild, Dr. -Ing. A. Gillner, "Laser Assisted Bonding of Silicon and Glass in Micro-System Technology," 07/03 http://www.ilt.fhg.de/eng/jb00-s42.html				
AQ	Saman Dharmatileke et al, "Anodic Bonding of Glass to Glass and Silicon to Glass or Silicon to Silicon Through a Very Thick Thermally Grown SiO ₂ Layer," <i>Proceedings of IS 3M International Symposium on Smart Structures & Microsystems</i> , Hong Kong, October 19-21, 2000, p. 32. http://dolphin.eng.us.edu/projects/bonding/paper.pdf				
AR					
AS					
AT					
AU					
Examiner		/Long Pham/ (02/29/2008)		Date Considered	
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